Lead-free Green

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max
30V	26.5mΩ @ V_{GS} = 10V	5.8A
	32mΩ @ V_{GS} = 4.5V	5.0A

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

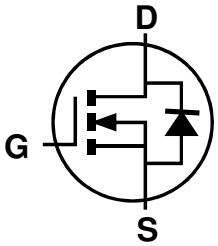
- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

Mechanical Data

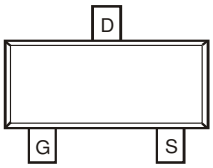
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

SOT23

Top View



Internal Schematic



Top View

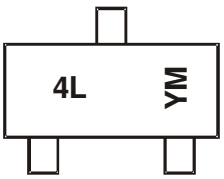
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3042L-7	SOT23	3,000/Tape & Reel
DMN3042L-13	SOT23	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information

SOT23



4L = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: B = 2014)
M = Month (ex: 9 = September)

Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015
Code	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	5.8 4.0	A
Maximum Body Diode Forward Current (Note 6)			I_S	1.5	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	30	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 5)		P_D	0.72	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	171	°C/W
Power Dissipation (Note 6)		P_D	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	93	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±12V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.6	—	1.4	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	21	26.5	mΩ	V_{GS} = 10V, I_D = 5.8A
		—	23	32		V_{GS} = 4.5V, I_D = 5.0A
		—	29	48		V_{GS} = 2.5V, I_D = 4.0A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	570	860	pF	V_{DS} = 15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	63	95		
Reverse Transfer Capacitance	C_{rss}	—	53	80		
Gate Resistance	R_G	—	3.2	4.5	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 10V)	Q_g	—	13.3	20	nC	V_{DS} = 15V, I_D = 6.9A
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	6.1	8		
Gate-Source Charge	Q_{gs}	—	1.0	1.5		
Gate-Drain Charge	Q_{gd}	—	1.6	2.5		
Turn-On Delay Time	$t_{D(on)}$	—	1.5	2.4	nS	V_{GS} = 10V, V_{DD} = 15V, R_G = 3Ω, I_D = 6.9A
Turn-On Rise Time	t_r	—	3.3	5		
Turn-Off Delay Time	$t_{D(off)}$	—	13.9	22		
Turn-Off Fall Time	t_f	—	4.9	7		
Body Diode Reverse Recovery Time	t_{rr}	—	7.8	12	nS	I_S = 5A, dI/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{rr}	—	1.9	3	nC	I_S = 5A, dI/dt = 100A/µs

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

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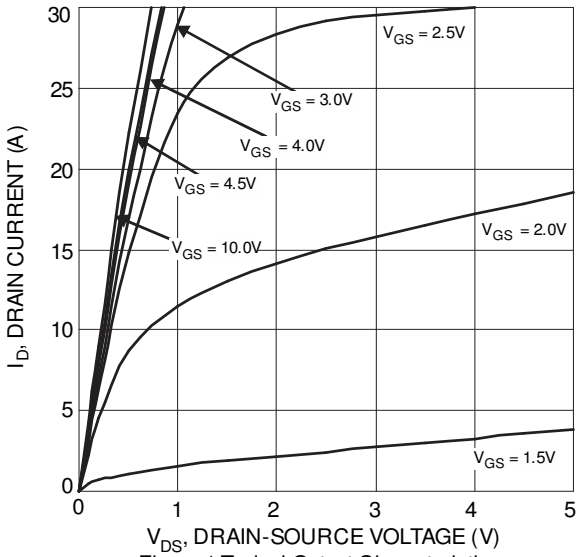

Figure 1 Typical Output Characteristics

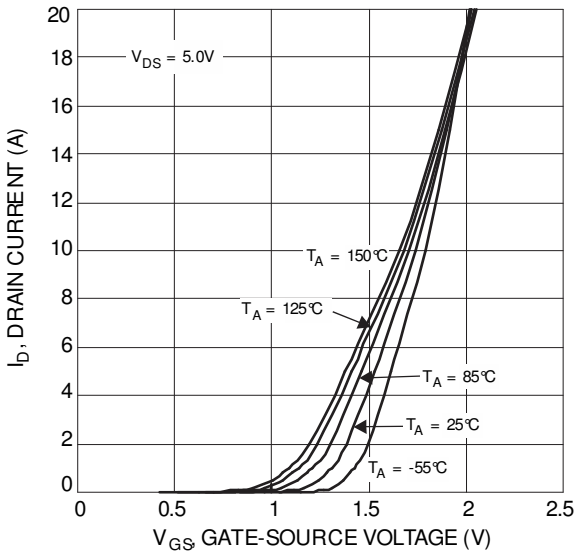

Figure 2 Typical Transfer Characteristics

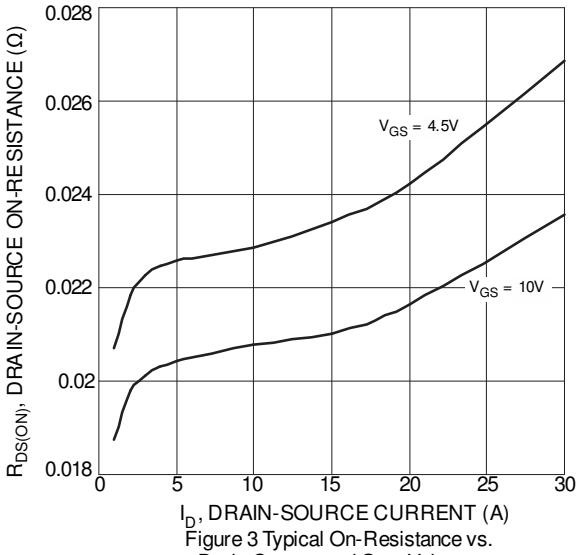

Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

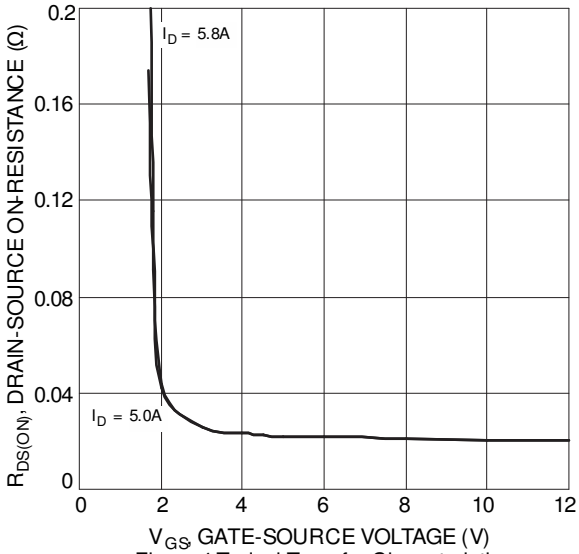

Figure 4 Typical Transfer Characteristic

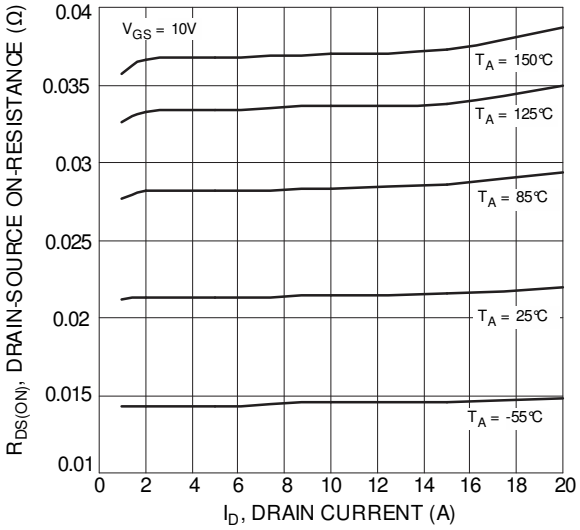

Figure 5 Typical On-Resistance vs. Drain Current and Temperature

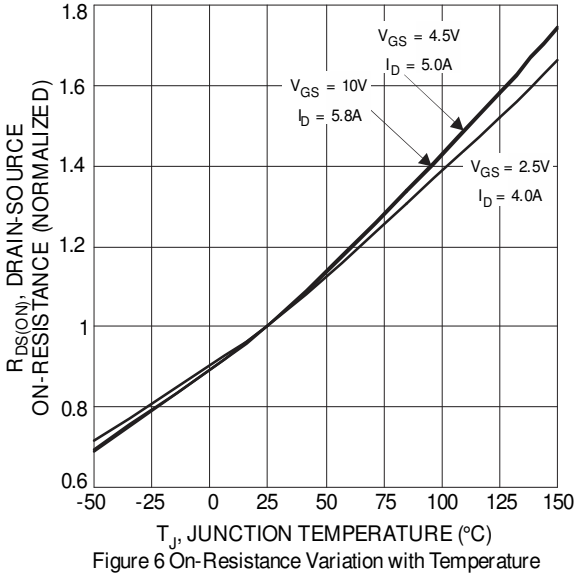

Figure 6 On-Resistance Variation with Temperature

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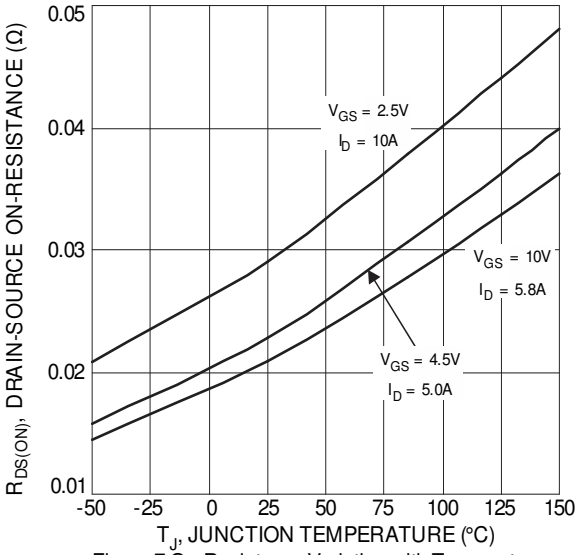

Figure 7 On-Resistance Variation with Temperature

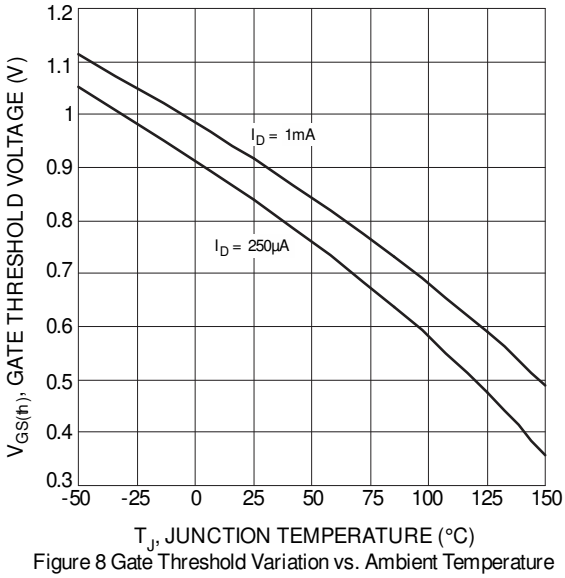

Figure 8 Gate Threshold Variation vs. Ambient Temperature

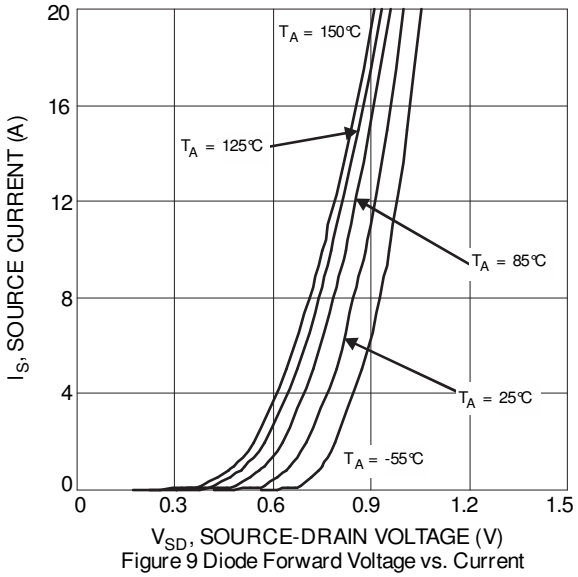

Figure 9 Diode Forward Voltage vs. Current

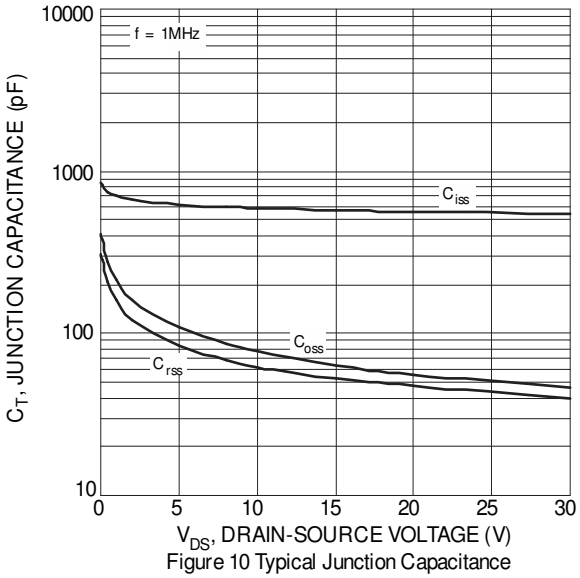

Figure 10 Typical Junction Capacitance

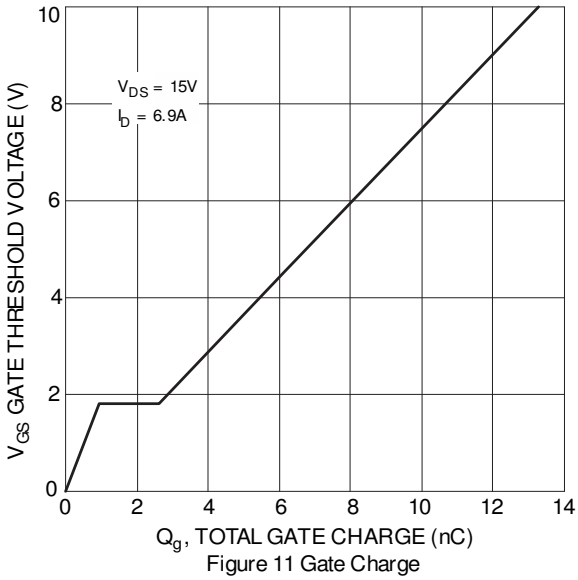

Figure 11 Gate Charge

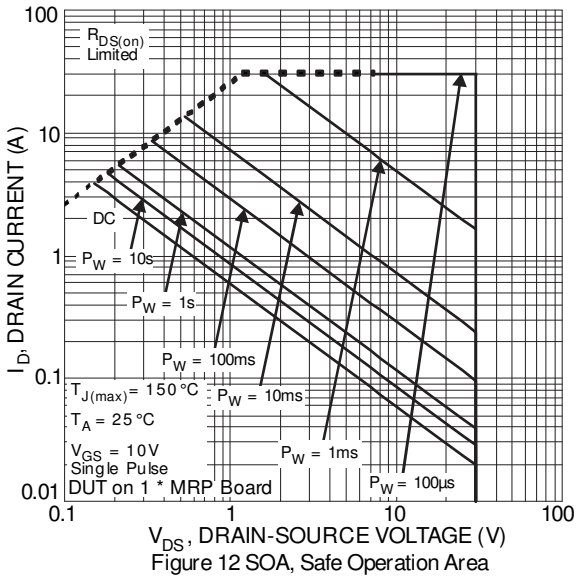

Figure 12 SOA, Safe Operation Area

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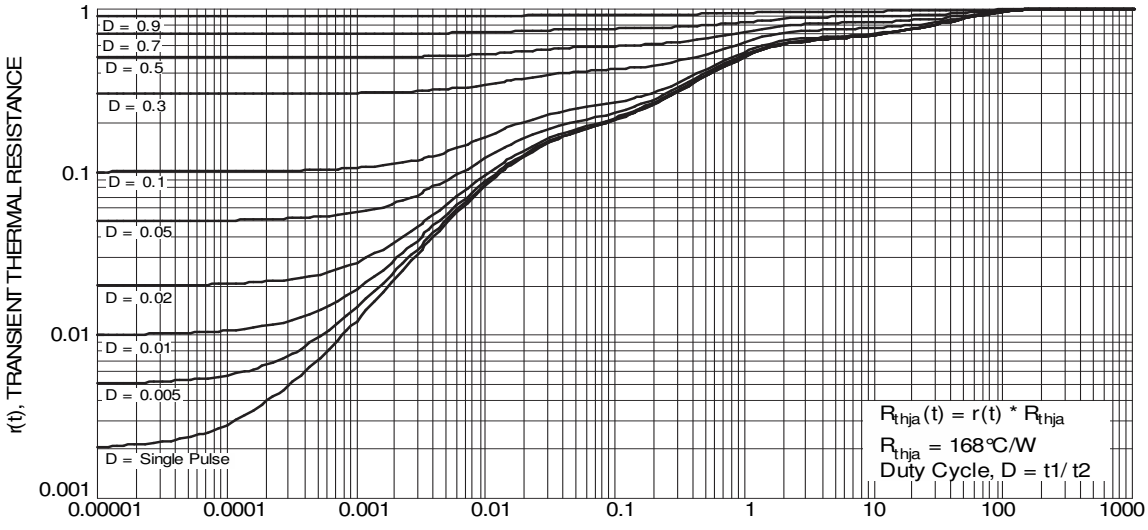
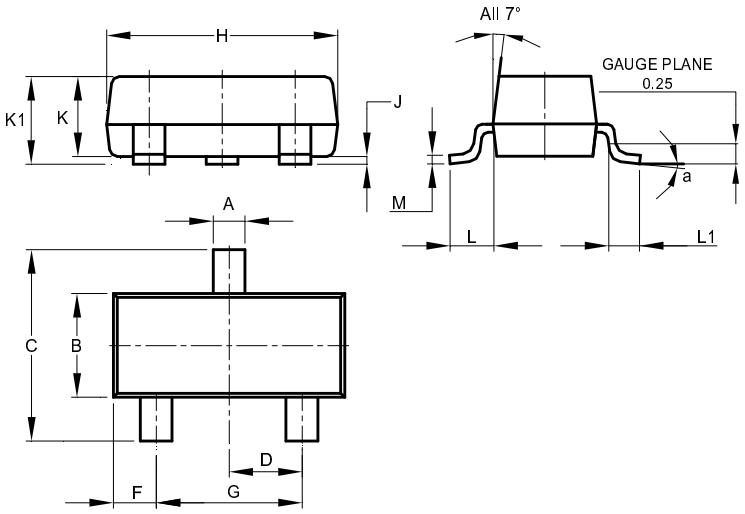


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

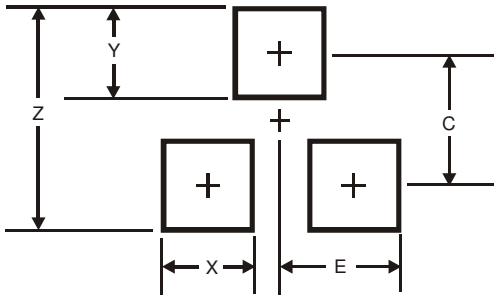
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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